

GaAs pHEMT MMIC MEDIUM POWER AMPLIFIER, 6 - 18 GHz

Typical Applications

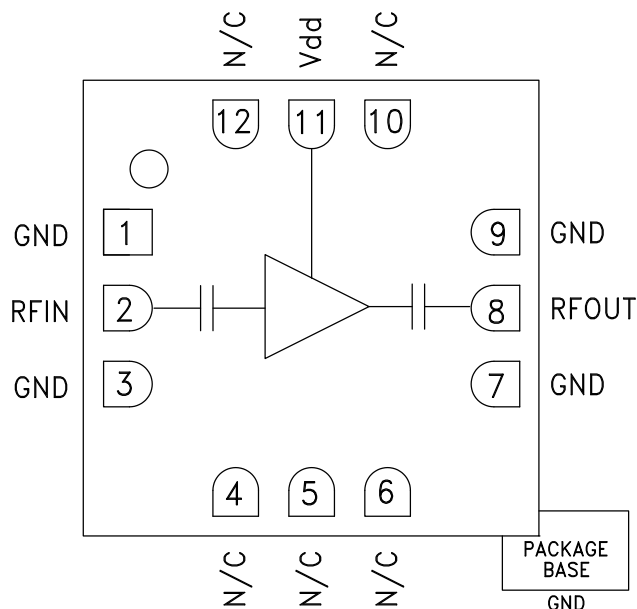
The HMC441LC3B is ideal for use as a medium power amplifier for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios & VSAT
- LO Driver for HMC Mixers
- Military EW & ECM

Features

- Gain: 14 dB
- Saturated Output Power: +21.5 dBm @ 27% PAE
- Single Positive Supply: +5V @ 90 mA
- 50 Ohm Matched Input/Output
- 12 Lead Ceramic 3x3mm SMT Package: 9mm²

Functional Diagram



General Description

The HMC441LC3B is an efficient GaAs PHEMT MMIC Medium Power Amplifier housed in a leadless RoHS compliant SMT package. Operating between 6 and 18 GHz, the amplifier provides 14 dB of gain, +21.5 dBm of saturated power and 27% PAE from a +5V supply. This 50 Ohm matched amplifier does not require any external components and operates from a single positive supply, making it an ideal linear gain block or driver for HMC SMT mixers. The HMC441LC3B is compatible with high volume surface mount manufacturing techniques, and the I/Os are DC blocked for further ease of integration.

Electrical Specifications, $T_A = +25^\circ\text{C}$, $V_{dd} = +5\text{V}$

| Parameter | Min. | Typ. | Max. | Min. | Typ. | Max. | Min. | Typ. | Max. | Min. | Typ. | Max. | Units |
|--|-----------|-------|------|------------|-------|------|-------------|-------|------|-------------|-------|------|-------|
| Frequency Range | 6.0 - 8.5 | | | 8.5 - 12.5 | | | 12.5 - 14.0 | | | 14.0 - 18.0 | | | GHz |
| Gain | 10 | 14 | 19 | 13 | 17 | 21 | 13 | 17 | 21 | 10 | 14 | 19 | dB |
| Gain Variation Over Temperature | | 0.015 | 0.02 | | 0.015 | 0.02 | | 0.015 | 0.02 | | 0.015 | 0.02 | dB/°C |
| Input Return Loss | | 10 | | | 13 | | | 20 | | | 13 | | dB |
| Output Return Loss | | 12 | | | 15 | | | 17 | | | 14 | | dB |
| Output Power for 1 dB Compression (P1dB) | 16 | 19 | | 17 | 20 | | 17 | 20 | | 17 | 20 | | dBm |
| Saturated Output Power (Psat) | | 20 | | | 21.5 | | | 22.5 | | | 21.5 | | dBm |
| Output Third Order Intercept (IP3) | 28 | 30 | | 29 | 32 | | 29 | 32 | | 29 | 32 | | dBm |
| Noise Figure | | 4.5 | 6 | | 4.5 | 6 | | 4.5 | 6 | | 4.5 | 6 | dB |
| Supply Current (I _{dd}) | | 90 | 115 | | 90 | 115 | | 90 | 115 | | 90 | 115 | mA |

HMC441LC3B* PRODUCT PAGE QUICK LINKS

Last Content Update: 10/05/2017

COMPARABLE PARTS

View a parametric search of comparable parts.

EVALUATION KITS

- HMC441LC3B Evaluation Board

DOCUMENTATION

Application Notes

- AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers
- Broadband Biasing of Amplifiers General Application Note
- MMIC Amplifier Biasing Procedure Application Note
- Thermal Management for Surface Mount Components General Application Note

Data Sheet

- HMC441LC3B: GaAs pHEMT MMIC Medium Power Amplifier, 6 - 18 GHz Data Sheet

TOOLS AND SIMULATIONS

- HMC441LC3B S-Parameters

REFERENCE MATERIALS

Quality Documentation

- Package/Assembly Qualification Test Report: LC3, LC3B, LC3C (QTR: 2014-00376 REV: 01)
- Semiconductor Qualification Test Report: PHEMT-F (QTR: 2013-00269)

DESIGN RESOURCES

- HMC441LC3B Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all HMC441LC3B EngineerZone Discussions.

SAMPLE AND BUY

Visit the product page to see pricing options.

TECHNICAL SUPPORT

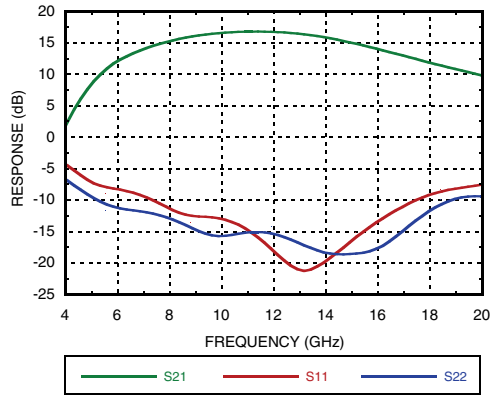
Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK

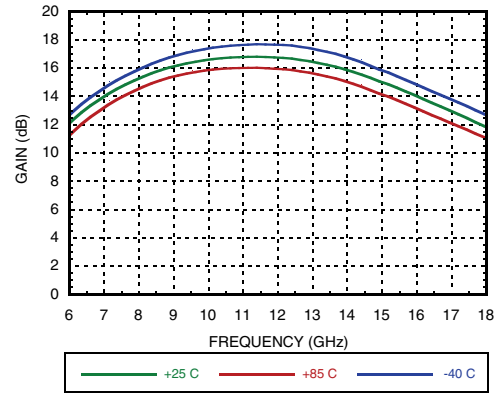
Submit feedback for this data sheet.

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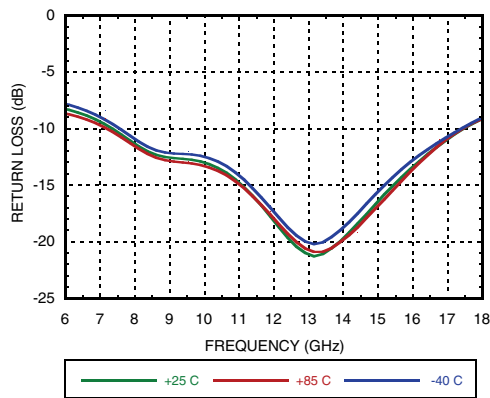
Broadband Gain & Return Loss



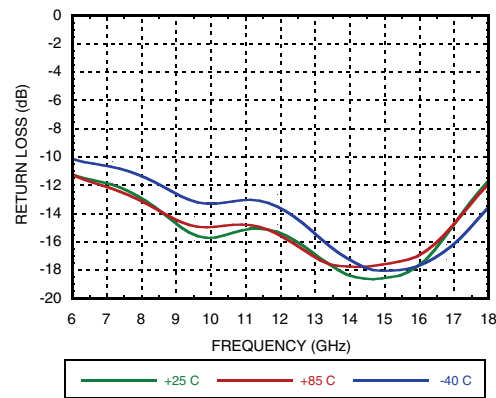
Gain vs. Temperature



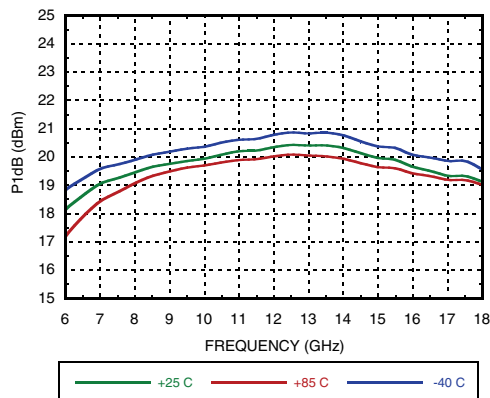
Input Return Loss vs. Temperature



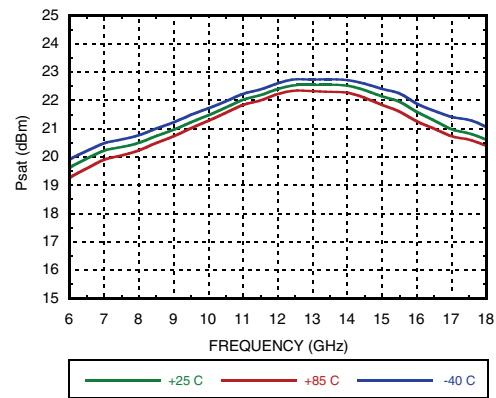
Output Return Loss vs. Temperature



P1dB vs. Temperature

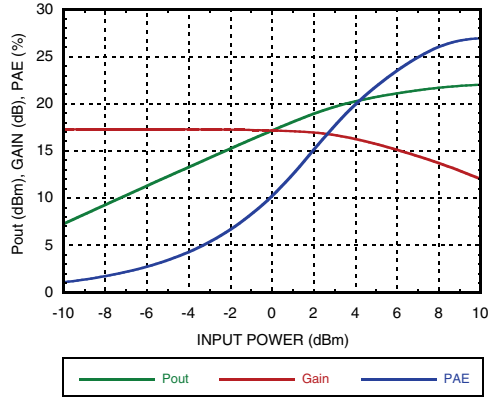


Psat vs. Temperature

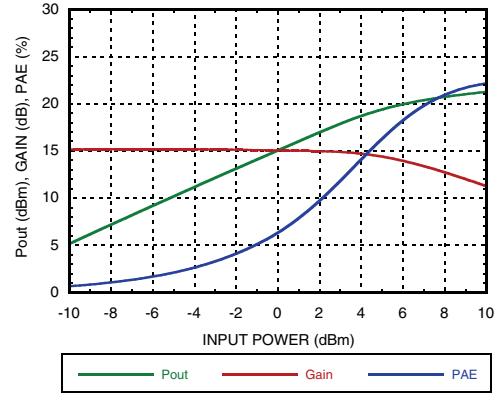


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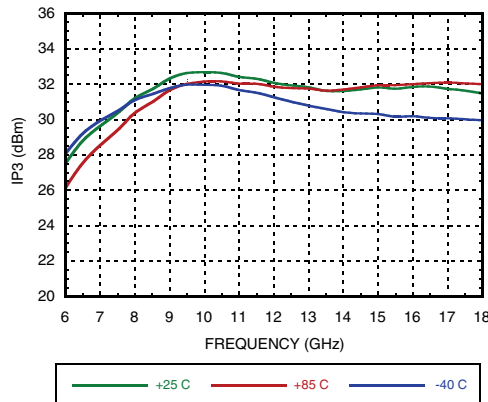
Power Compression @ 11 GHz



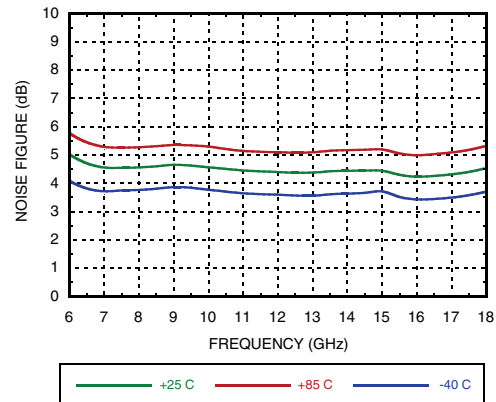
Power Compression @ 15 GHz



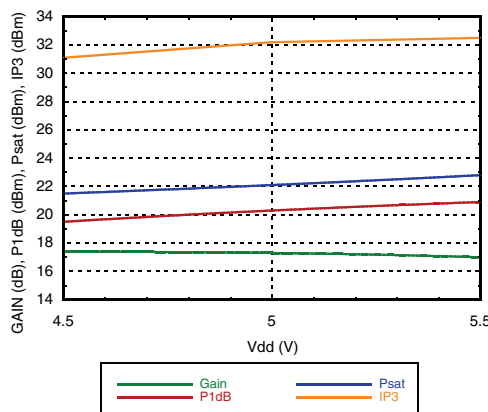
Output IP3 vs. Temperature



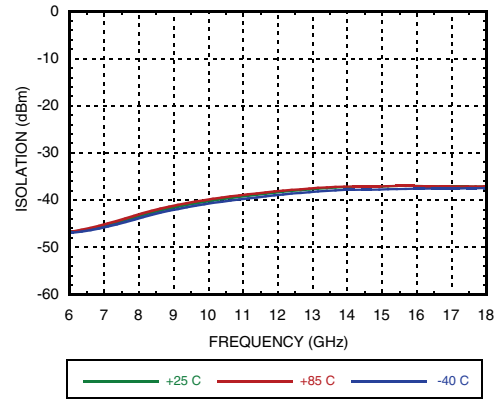
Noise Figure vs. Temperature



Gain, Power & Output IP3 vs. Supply Voltage @ 11 GHz

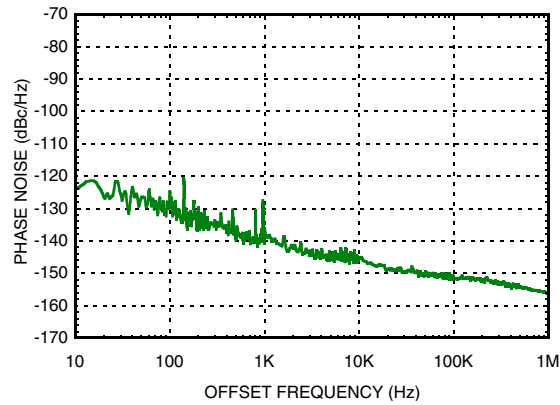


Reverse Isolation vs. Temperature



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**Additive Phase Noise Vs Offset Frequency,
RF Frequency = 8 GHz,
RF Input Power = 5 dBm (P1dB)**



Notes:

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Absolute Maximum Ratings

| | |
|--|----------------------|
| Drain Bias Voltage (Vdd) | +6 Vdc |
| RF Input Power (RFIN)(Vdd = +5 Vdc) | +15 dBm |
| Channel Temperature | 175 °C |
| Continuous P _{diss} (T = 85 °C) (derate 8.2 mW/°C above 85 °C) | 0.74 W |
| Thermal Resistance (channel to ground paddle) | 122 °C/W |
| Storage Temperature | -65 to +150 °C |
| Operating Temperature | -40 to +85 °C |
| ESD Sensitivity (HBM) | Class 0, Passed 100V |

Typical Supply Current vs. Vdd

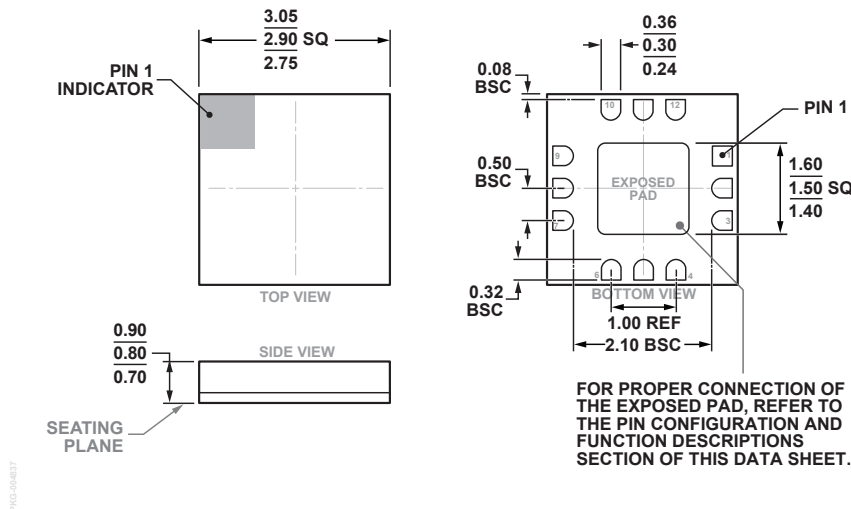
| Vdd (V) | I _{dd} (mA) |
|---------|----------------------|
| +5.5 | 92 |
| +5.0 | 90 |
| +4.5 | 88 |

Note: Amplifier will operate over full voltage range shown above



**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**

Outline Drawing



12-Terminal Ceramic Leadless Chip Carrier [LCC]
(E-12-4)
Dimensions shown in millimeters

Package Information

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking ^[2] |
|-------------|-----------------------|------------------|---------------------|--------------------------------|
| HMC441LC3B | Alumina, White | Gold over Nickel | MSL3 ^[1] | H441 XXXX |

[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX

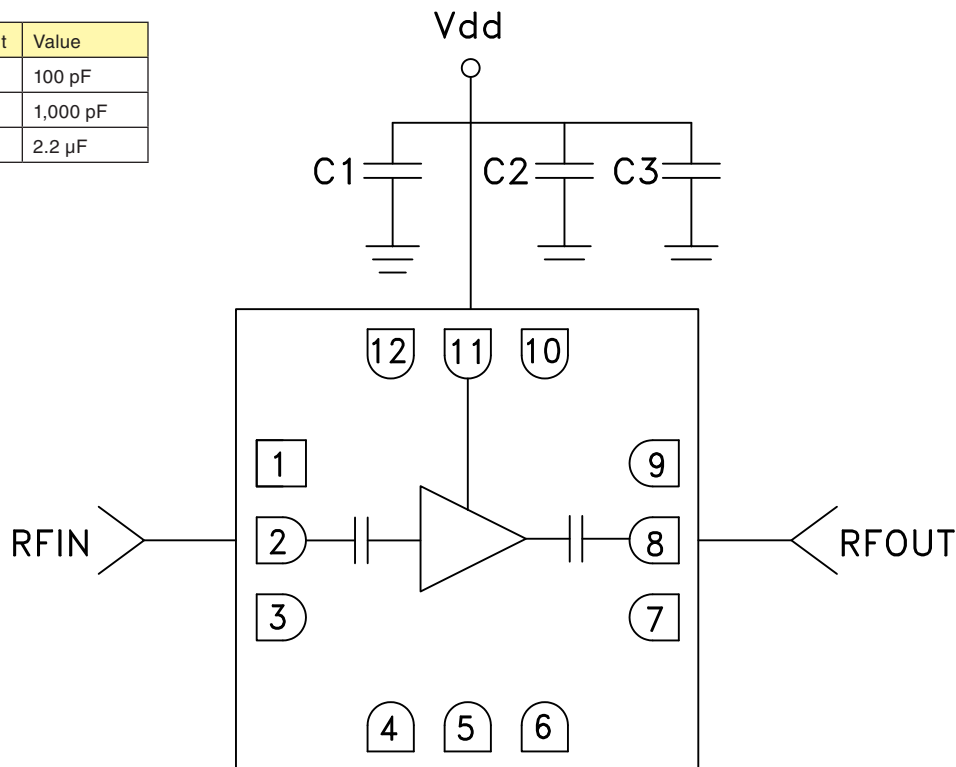
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Pin Descriptions

| Pin Number | Function | Description | Interface Schematic |
|-----------------|----------|--|---------------------|
| 1, 3, 7, 9 | GND | Package bottom must also be connected to RF/DC ground | |
| 2 | RFIN | This pin is AC coupled and matched to 50 Ohms. | |
| 4 - 6 10, 12 | N/C | This pin may be connected to RF/DC ground. Performance will not be affected. | |
| 8 | RFOUT | This pin is AC coupled and matched to 50 Ohms. | |
| 11 | Vdd | Power Supply Voltage for the amplifier. External bypass capacitors are required. | |

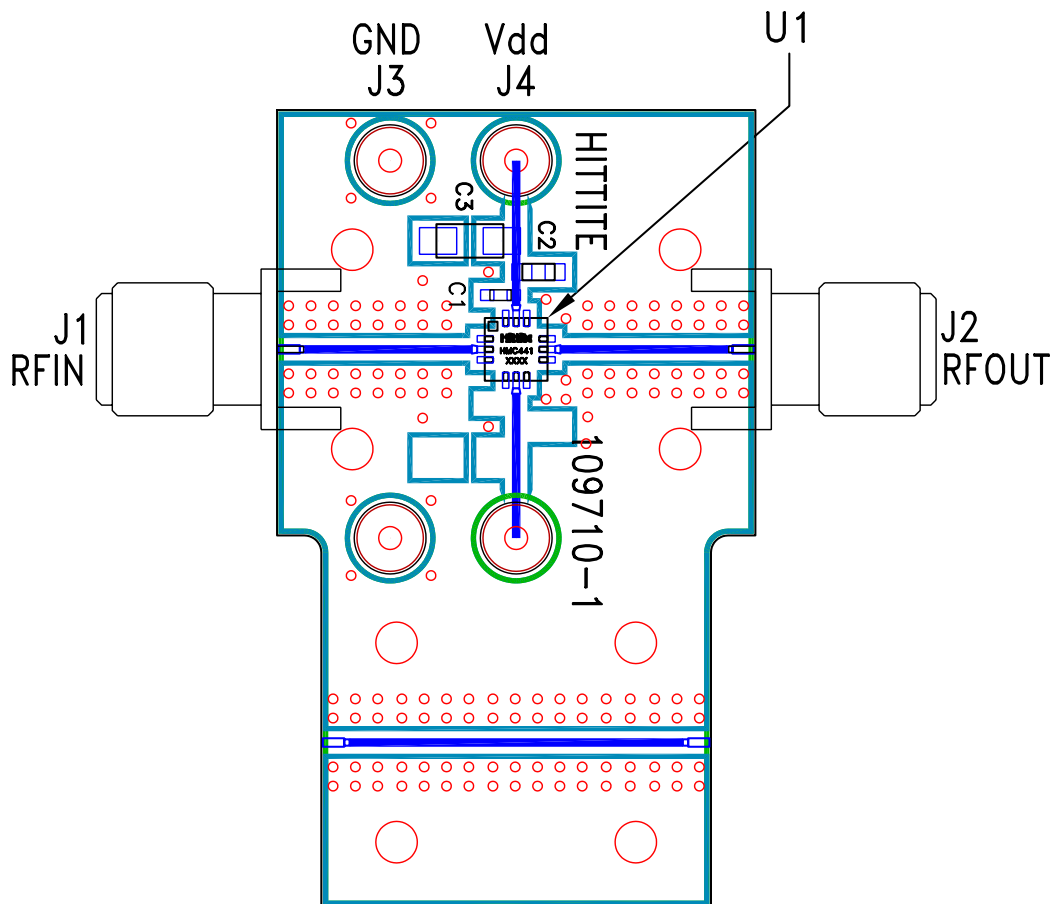
Application Circuit

| Component | Value |
|-----------|-------------|
| C1 | 100 pF |
| C2 | 1,000 pF |
| C3 | 2.2 μ F |



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Evaluation PCB



List of Materials for Evaluation PCB 109712 [1]

| Item | Description |
|---------|---------------------------------|
| J1 - J2 | PCB Mount SMA Connector |
| J3 - J4 | DC Pin |
| C1 | 100 pF Capacitor, 0402 Pkg. |
| C2 | 1000 pF Capacitor, 0603 Pkg. |
| C3 | 2.2 μ F Capacitor, Tantalum |
| U1 | HMC441LC3B Amplifier |
| PCB [2] | 109710 Evaluation PCB, 10 mils |

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Analog Devices upon request.